

# 3-Input OR Gate with Schmitt-Trigger Inputs

## SL17SZS332

The SL17SZS332 is a 3-Input OR Gate with Schmitt-trigger Inputs in a tiny footprint package.

### Features

- Designed for 1.65 V to 5.5 V  $V_{CC}$  Operation
- 2.7 ns  $t_{PD}$  at  $V_{CC} = 5$  V (typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- $I_{OFF}$  Supports Partial Power Down Protection
- Source/Sink 24 mA at 3.0 V
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

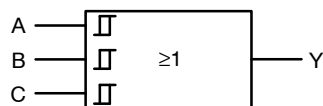


Figure 1. Logic Symbol



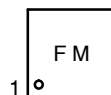
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### MARKING DIAGRAM



**UDFN6**  
**1.0 x 1.0**  
**CASE 517BX**



F = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

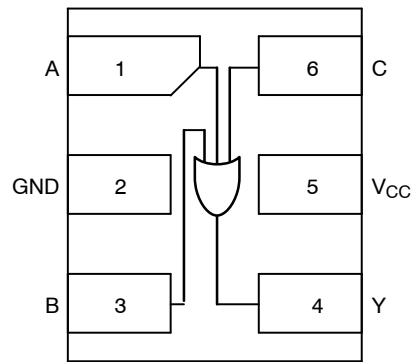
(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 7 of this data sheet.

# SL17SZS332



**Figure 2. Pinout (Top View)**

## PIN ASSIGNMENT

Pin	Function
1	A
2	GND
3	B
4	Y
5	V <sub>CC</sub>
6	C

## FUNCTION TABLE

Input			Output
A	B	C	Y
L	L	L	L
L	L	H	H
L	H	L	H
L	H	H	H
H	L	L	H
H	L	H	H
H	H	L	H
H	H	H	H

**MAXIMUM RATINGS**

Symbol	Characteristics	Value	Unit
$V_{CC}$	DC Supply Voltage	-0.5 to +6.5	V
$V_{IN}$	DC Input Voltage	-0.5 to +6.5	V
$V_{OUT}$	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode ( $V_{CC} = 0$ V)	-0.5 to $V_{CC} + 0.5$ -0.5 to +6.5 -0.5 to +6.5	V
$I_{IK}$	DC Input Diode Current $V_{IN} < GND$	-50	mA
$I_{OK}$	DC Output Diode Current $V_{OUT} < GND$	-50	mA
$I_{OUT}$	DC Output Source/Sink Current	$\pm 50$	mA
$I_{CC}$ or $I_{GND}$	DC Supply Current per Supply Pin or Ground Pin	$\pm 100$	mA
$T_{STG}$	Storage Temperature Range	-65 to +150	°C
$T_L$	Lead Temperature, 1 mm from Case for 10 secs	260	°C
$T_J$	Junction Temperature Under Bias	+150	°C
$\theta_{JA}$	Thermal Resistance (Note 2)	382	°C/W
$P_D$	Power Dissipation in Still Air	327	mW
MSL	Moisture Sensitivity	Level 1	-
$F_R$	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
$V_{ESD}$	ESD Withstand Voltage (Note 3) Human Body Model Charged Device Model	2000 1000	V
$I_{Latchup}$	Latchup Performance (Note 4)	$\pm 100$	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.
2. Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow.
3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Characteristics	Min	Max	Unit
$V_{CC}$	Positive DC Supply Voltage	1.65	5.5	V
$V_{IN}$	DC Input Voltage	0	5.5	V
$V_{OUT}$	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode ( $V_{CC} = 0$ V)	0 0 0	$V_{CC}$ 5.5 5.5	
$T_A$	Operating Temperature Range	-55	+125	°C
$t_r, t_f$	Input Rise and Fall Time $V_{CC} = 1.65$ V to 1.95 V $V_{CC} = 2.3$ V to 2.7 V $V_{CC} = 3.0$ V to 3.6 V $V_{CC} = 4.5$ V to 5.5 V	0 0 0 0	No Limit No Limit No Limit No Limit	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			-55°C ≤ T <sub>A</sub> ≤ 125°C		Units
				Min	Typ	Max	Min	Max	
V <sub>T+</sub>	Positive Input Threshold Voltage		1.65	–	1.0	1.4	–	1.4	V
			2.3	–	1.5	1.8	–	1.8	
			2.7	–	1.7	2.0	–	2.0	
			3.0	–	1.9	2.2	–	2.2	
			4.5	–	2.7	3.1	–	3.1	
			5.5	–	3.3	3.6	–	3.6	
V <sub>T–</sub>	Negative Input Threshold Voltage		1.65	0.2	0.5	–	0.2	–	V
			2.3	0.4	0.75	–	0.4	–	
			2.7	0.5	0.87	–	0.5	–	
			3.0	0.6	1.0	–	0.6	–	
			4.5	1.0	1.5	–	1.0	–	
			5.5	1.2	1.9	–	1.2	–	
V <sub>H</sub>	Input Hysteresis Voltage		1.65	0.1	0.48	0.9	0.1	0.9	V
			2.3	0.25	0.75	1.1	0.25	1.1	
			2.7	0.3	0.83	1.15	0.3	1.15	
			3.0	0.4	0.93	1.2	0.4	1.2	
			4.5	0.6	1.2	1.5	0.6	1.5	
			5.5	0.7	1.4	1.7	0.7	1.7	
V <sub>OH</sub>	High-Level Output Voltage	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	1.65 to 5.5	V <sub>CC</sub> – 0.1	V <sub>CC</sub>	–	V <sub>CC</sub> – 0.1	–	V
		I <sub>OH</sub> = –100 μA	1.65	1.29	1.4	–	1.29	–	
		I <sub>OH</sub> = –4 mA	2.3	1.9	–	–	1.9	–	
		I <sub>OH</sub> = –8 mA	2.7	2.2	2.1	–	2.2	–	
		I <sub>OH</sub> = –12 mA	3.0	2.4	2.4	–	2.4	–	
		I <sub>OH</sub> = –16 mA	3.0	2.4	2.7	–	2.4	–	
		I <sub>OH</sub> = –24 mA	3.0	2.3	2.5	–	2.3	–	
		I <sub>OH</sub> = –32 mA	4.5	3.8	4.0	–	3.8	–	
V <sub>OL</sub>	Low-Level Output Voltage	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	1.65 to 5.5	–	–	0.1	–	0.1	V
		I <sub>OL</sub> = 100 μA	1.65	–	0.08	0.24	–	0.24	
		I <sub>OL</sub> = 4 mA	2.3	–	0.2	0.3	–	0.3	
		I <sub>OL</sub> = 8 mA	2.7	–	0.22	0.4	–	0.4	
		I <sub>OL</sub> = 12 mA	3.0	–	0.28	0.4	–	0.4	
		I <sub>OL</sub> = 16 mA	3.0	–	0.38	0.55	–	0.55	
		I <sub>OL</sub> = 24 mA	3.0	–	0.38	0.55	–	0.55	
		I <sub>OL</sub> = 32 mA	4.5	–	0.42	0.55	–	0.55	
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	1.65 to 5.5	–	–	±0.1	–	±1.0	μA
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V	0	–	–	1.0	–	10	μA
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5	–	–	1.0	–	10	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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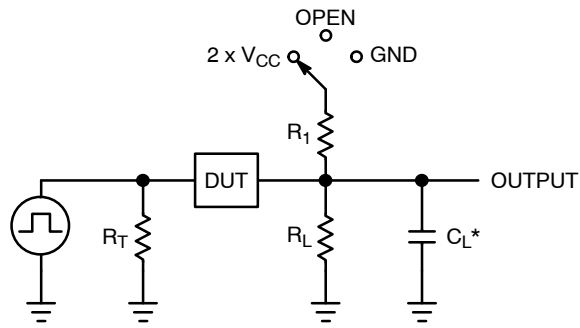
## AC ELECTRICAL CHARACTERISTICS ( $t_R = t_F = 3.0$ ns)

Symbol	Parameter	Condition	$V_{CC}$ (V)	$T_A = 25^\circ\text{C}$			$-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$		Units
				Min	Typ	Max	Min	Max	
$t_{PLH}$ $t_{PHL}$	Propagation Delay, A to Y (Figures 3 and 4)	$R_L = 1\text{ M}\Omega$ , $C_L = 15\text{ pF}$	1.65 to 1.95	–	5.5	12	–	12.7	ns
		$R_L = 1\text{ M}\Omega$ , $C_L = 15\text{ pF}$	2.3 to 2.7	–	3.0	7.0	–	7.5	
		$R_L = 1\text{ M}\Omega$ , $C_L = 15\text{ pF}$	3.0 to 3.6	–	2.6	4.7	–	5.0	
		$R_L = 500\text{ }\Omega$ , $C_L = 50\text{ pF}$		–	3.0	5.2	–	5.5	
		$R_L = 1\text{ M}\Omega$ , $C_L = 15\text{ pF}$	4.5 to 5.5	–	2.4	4.1	–	4.4	
		$R_L = 500\text{ }\Omega$ , $C_L = 50\text{ pF}$		–	2.7	4.5	–	4.8	

## CAPACITIVE CHARACTERISTICS ( $t_R = t_F = 3.0$ ns)

Symbol	Parameter	Condition	Typical	Units
$C_{IN}$	Input Capacitance	$V_{CC} = 5.5\text{ V}$ , $V_{IN} = 0\text{ V}$ or $V_{CC}$	2.5	pF
$C_{OUT}$	Output Capacitance	$V_{CC} = 5.5\text{ V}$ , $V_{IN} = 0\text{ V}$ or $V_{CC}$	2.5	pF
$C_{PD}$	Power Dissipation Capacitance (Note 5)	10 MHz, $V_{CC} = 3.3\text{ V}$ , $V_{IN} = 0\text{ V}$ or $V_{CC}$ 10 MHz, $V_{CC} = 5.5\text{ V}$ , $V_{IN} = 0\text{ V}$ or $V_{CC}$	9 11	pF

5.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}$ .  $C_{PD}$  is used to determine the no-load dynamic power consumption;  $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$ .



$C_L$  includes probe and jig capacitance  
 $R_T$  is  $Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )  
 $f = 1$  MHz

Figure 3. Test Circuit

Test	Switch Position	$C_L$ , pF	$R_L$ , $\Omega$	$R_1$ , $\Omega$
$t_{PLH} / t_{PHL}$	Open	See AC Characteristics Table		
$t_{PLZ} / t_{PZL}$	$2 \times V_{CC}$	50	500	500
$t_{PHZ} / t_{PZH}$	GND	50	500	500

X = Don't Care

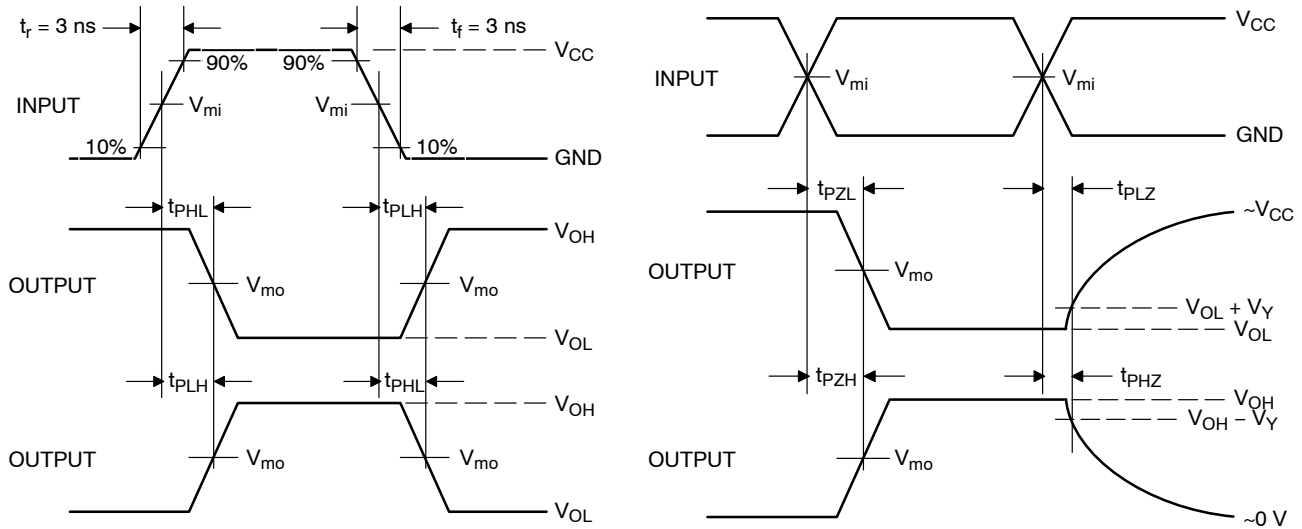


Figure 4. Switching Waveforms

$V_{CC}$ , V	$V_{mi}$ , V	$V_{mo}$ , V		$V_Y$ , V
		$t_{PLH}, t_{PHL}$	$t_{PZL}, t_{PLZ}, t_{PZH}, t_{PHZ}$	
1.65 to 1.95	$V_{CC}/2$	$(V_{OH} - V_{OL})/2$	$V_{CC}/2$	0.15
2.3 to 2.7	$V_{CC}/2$	$(V_{OH} - V_{OL})/2$	$V_{CC}/2$	0.15
3.0 to 3.6	$V_{CC}/2$	$(V_{OH} - V_{OL})/2$	$V_{CC}/2$	0.3
4.5 to 5.5	$V_{CC}/2$	$(V_{OH} - V_{OL})/2$	$V_{CC}/2$	0.3

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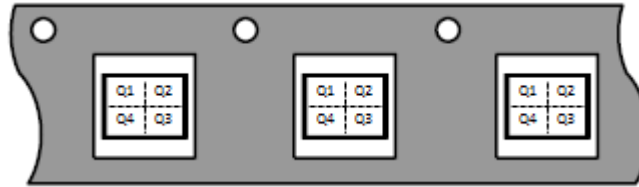
### DEVICE ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping <sup>†</sup>
SL17SZS332MU3TCG	UDFN6, 1 x 1, 0.35P	F	Q4	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### Pin 1 Orientation in Tape and Reel

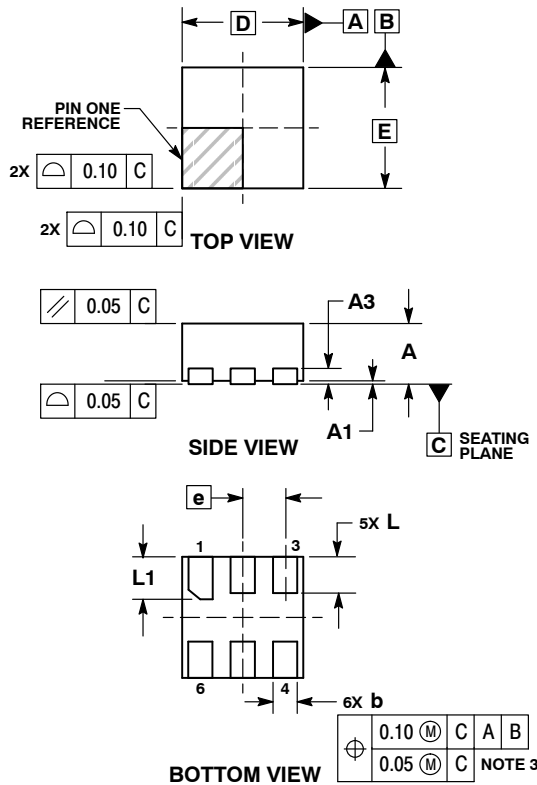
Direction of Feed



# SL17SZS332

## PACKAGE DIMENSIONS

UDFN6, 1x1, 0.35P  
CASE 517BX  
ISSUE O

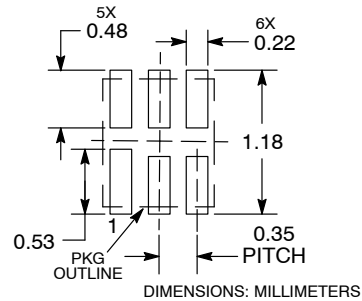


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13	REF
b	0.12	0.22
D	1.00	BSC
E	1.00	BSC
e	0.35	BSC
L	0.25	0.35
L1	0.30	0.40

### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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